Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:

Metal

Overall Length:

0.405 inches

Mounting Facility Quantity:

1

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

Do-4

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Overall Width Across Flats:

0.437 inches

Thread Size:

0.190 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

100.0 repetitive peak reverse voltage and 70.0 reverse voltage, total rms

Current Rating Per Characteristic:

80.00 amperes forward current, average blank and 300.00 amperes forward current, average preset and 20.00 amperes forward current, total rms megahertz

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius junction

Test Data Document:

95542-141-128 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unf

Terminal Type And Quantity:

1 tab, solder lug and 1 threaded stud

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

Fiig:

A110a0